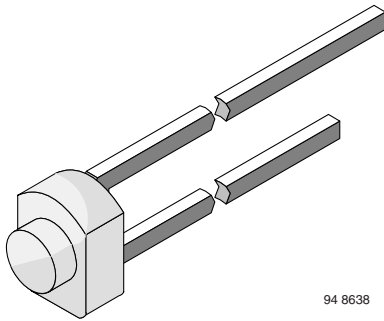


Silicon NPN Phototransistor, RoHS Compliant



94 8638

FEATURES

- Package type: leaded
- Package form: T-3/4
- Dimensions (in mm): Ø 1.8
- High photo sensitivity
- High radiant sensitivity
- Suitable for visible and near infrared radiation
- Fast response times
- Angle of half sensitivity: $\varphi = \pm 40^\circ$
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC



RoHS
COMPLIANT

DESCRIPTION

BPW16N is a silicon NPN phototransistor with high radiant sensitivity in clear, T-3/4 plastic package with flat window. It is sensitive to visible and near infrared radiation. On PCB this package size enables assembly of arrays with 2.54 mm pitch.

APPLICATIONS

- Detector in electronic control and drive circuits

PRODUCT SUMMARY			
COMPONENT	I_{ca} (mA)	φ (deg)	$\lambda_{0.1}$ (nm)
BPW16N	0.14	± 40	450 to 1040

Note

Test condition see table "Basic Characteristics"

ORDERING INFORMATION			
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
BPW16N	Bulk	MOQ: 5000 pcs, 5000 pcs/bulk	T-3/4

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Collector emitter voltage		V_{CEO}	32	V
Emitter collector voltage		V_{ECO}	5	V
Collector current		I_C	50	mA
Collector peak current	$t_p/T = 0.5; t_p \leq 10$ ms	I_{CM}	100	mA
Power dissipation	$T_{amb} \leq 55$ °C	P_V	100	mW
Junction temperature		T_j	100	°C
Operating temperature range		T_{amb}	- 40 to + 100	°C
Storage temperature range		T_{stg}	- 40 to + 100	°C
Soldering temperature	$t \leq 3$ s	T_{sd}	260	°C
Thermal resistance junction/ambient	Connected with Cu wire, 0.14 mm ²	R_{thJA}	450	K/W

Note

$T_{amb} = 25$ °C, unless otherwise specified

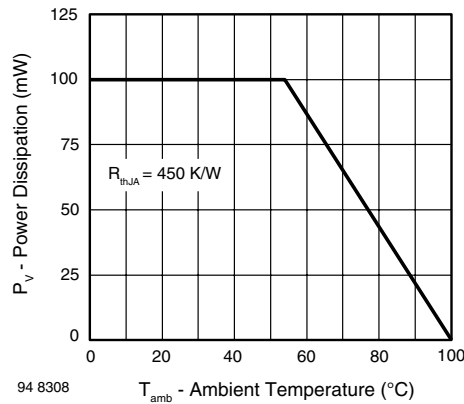


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Collector emitter breakdown voltage	$I_C = 1 \text{ mA}$	$V_{(BR)CEO}$	32			V
Collector emitter dark current	$V_{CE} = 20 \text{ V}, E = 0$	I_{CEO}		1	200	nA
Collector emitter capacitance	$V_{CE} = 5 \text{ V}, f = 1 \text{ MHz}, E = 0$	C_{CEO}		8		pF
Collector light current	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}, V_{CE} = 5 \text{ V}$	I_{ca}	0.07	0.14		mA
Angle of half sensitivity		φ		± 40		deg
Wavelength of peak sensitivity		λ_p		825		nm
Range of spectral bandwidth		$\lambda_{0.1}$		450 to 1040		nm
Collector emitter saturation voltage	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}, I_C = 0.01 \text{ mA}$	V_{CEsat}			0.3	V
Turn-on time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$	t_{on}		4.8		μs
Turn-off time	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$	t_{off}		5.0		μs
Cut-off frequency	$V_S = 5 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$	f_c		120		kHz

Note
 $T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified

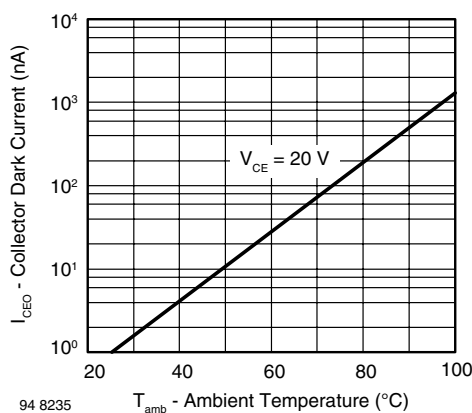
BASIC CHARACTERISTICS
 $T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified


Fig. 2 - Collector Dark Current vs. Ambient Temperature

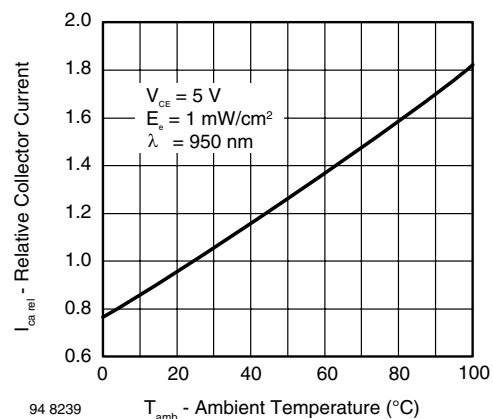


Fig. 3 - Relative Collector Current vs. Ambient Temperature

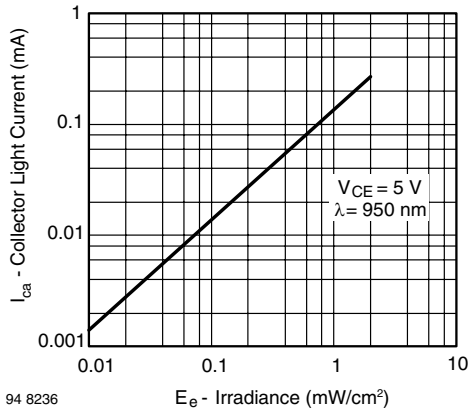


Fig. 4 - Collector Light Current vs. Irradiance

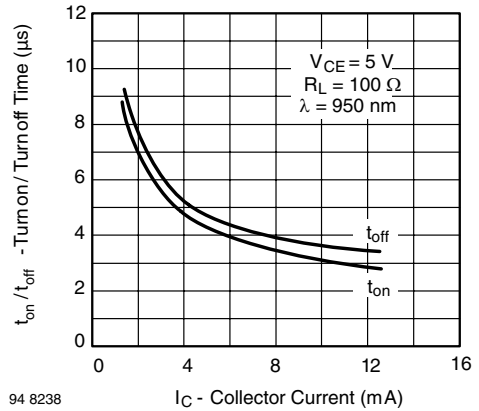


Fig. 7 - Turn-on/Turn-off Time vs. Collector Current

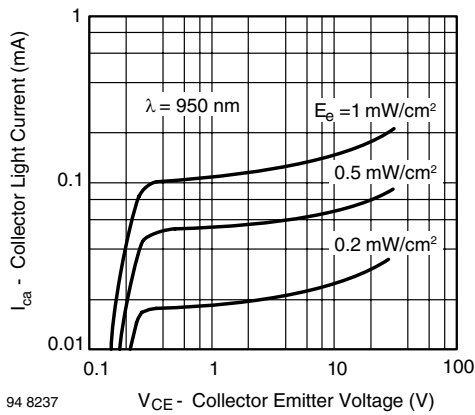


Fig. 5 - Collector Light Current vs. Collector Emitter Voltage

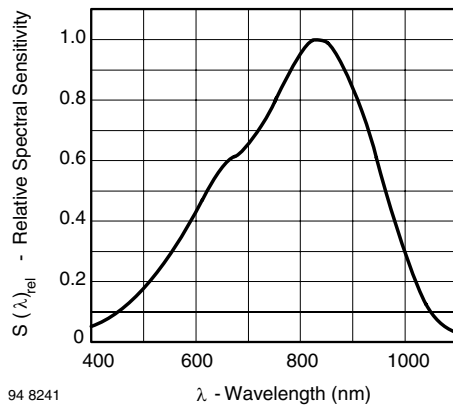


Fig. 8 - Relative Spectral Sensitivity vs. Wavelength

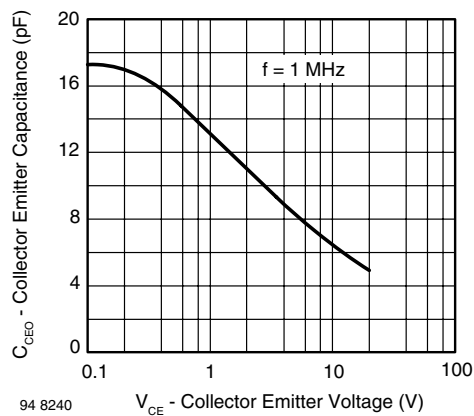


Fig. 6 - Collector Emitter Capacitance vs. Collector Emitter Voltage

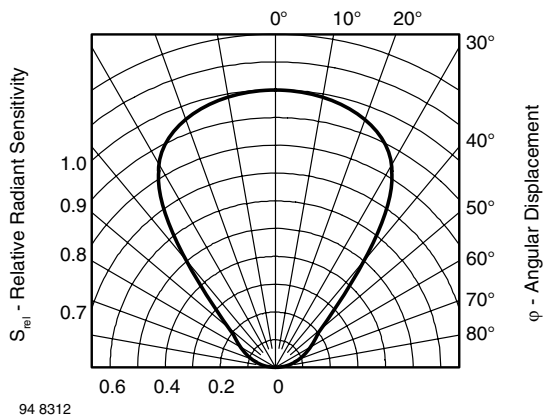
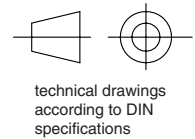
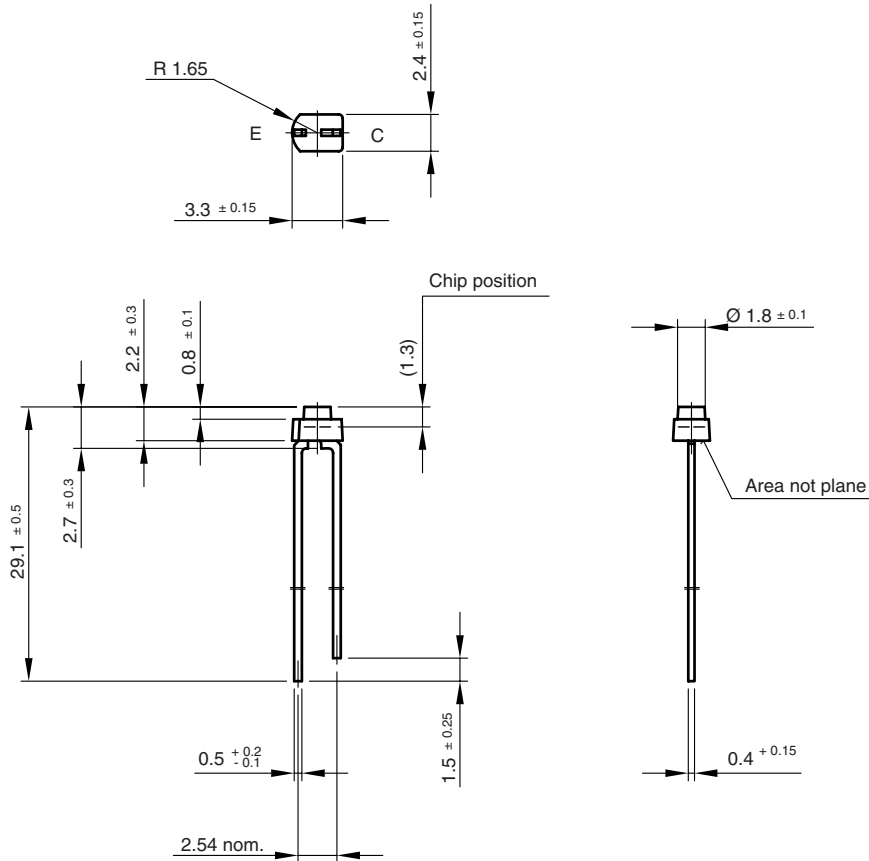


Fig. 9 - Relative Radiant Sensitivity vs. Angular Displacement



PACKAGE DIMENSIONS in millimeters



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